

3. (Cancelled)
4. (Cancelled)
5. (Cancelled)
6. (Cancelled)
7. (Cancelled)
8. (Currently Amended) A stacked die package comprising:  
a package substrate having a top side and a bottom side, the top side having a plurality of bond pads provided thereon, and the bottom side having a ball-grid array pattern provided thereon;  
a first semiconductor device mounted on the top side of the package substrate, the first semiconductor device having a plurality of bond pads provided thereon;  
a silicon interposer mounted on the first semiconductor device, the interposer having a first interposer bond pad and a second interposer bond pad, both lying outside a perimeter of the first semiconductor device, wherein the first and second interposer bond pads are electrically coupled via a conductive trace, and wherein the interposer includes: an interposer substrate; a dielectric layer formed on the interposer substrate; a conductive trace formed on the dielectric layer; and a passivation layer formed on the conductive trace, said passivation layer having a plurality of windows formed therein to expose the conductive trace in areas defining the interposer bond pads; and  
a second semiconductor device mounted on the interposer, the second semiconductor device having a plurality of bond pads provided thereon, wherein said conductive trace lies at least partially underneath said second semiconductor device;

a first bond wire connected to one of the plurality of bond pads on said first semiconductor and to the first interposer bond pad;

a second bond wire connected to the second interposer bond pad and to one of the plurality of bond pads on the semiconductor device; and

a third bond wire connected to one of the plurality of bond pads on the top side of the package substrate and to a bond pad on the first semiconductor device

9. (New) The stacked die package of claim 8, wherein said interposer substrate comprises silicon.
10. (New) The stacked die package of claim 8, wherein said package substrate comprises a material selected from the group consisting of ceramic, polyimide, metal, glass-filled resin, cyanate-glass.
11. (New) The stacked die package of claim 8, wherein said package substrate includes multilevel metallization.
12. (New) The stacked die package of claim 8, wherein said interposer passivation layer comprises silicon nitride